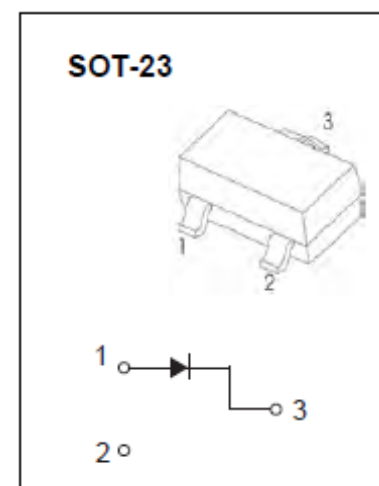
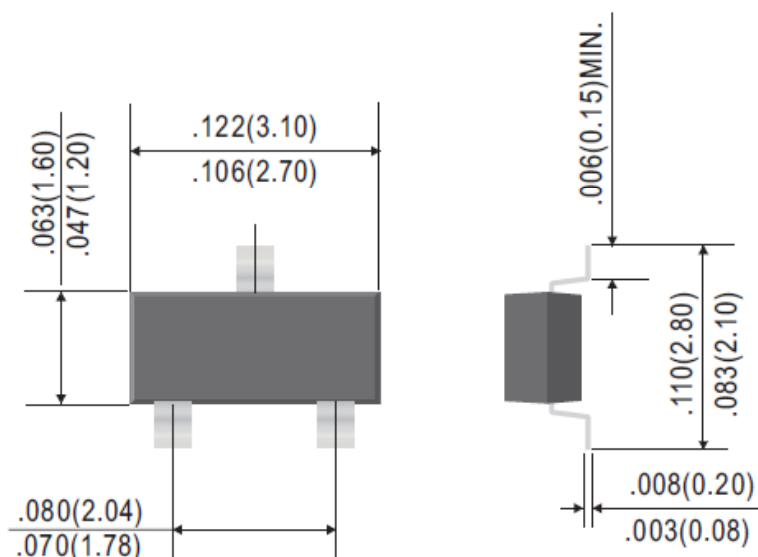


Dimensions in inches and (millimeters)

FEATURES

- Fast Switching Speed
- High Conductance
- High Reverse Breakdown Voltage Rating
- We declare that the material of product compliance with RoHS requirements.
- Pb-Free package is available
- RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1

MARKING: KAE

High Voltage Surface Mount Switching Diode

Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)			
Characteristic	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	350	V
Working Peak Reverse Voltage	V_{RWM}	300	V
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	212	V
Forward Continuous Current (Note 2)	I_F	225	mA
Peak Repetitive Forward Current (Note 2)	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current		@ $t=1.0\mu\text{s}$	4
		@ $t=1.0\text{s}$	1
Power Dissipation (Note 2)	P_D	350	mW
Thermal Resistance from Junction to Ambient (Note 2)	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Operating/ Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)						
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage (Note 1)	$V_{(BR)}$	$I_R=100\mu\text{A}$	350	—	—	V
Reverse Current (Note 1)	I_R	$V_R=240\text{V}$	—	30	100	nA
		$V_R=240\text{V}, T_J=150^{\circ}\text{C}$	—	35	100	μA
Forward Voltage (Note 1)	V_F	$I_F=20\text{mA}$	—	0.78	0.87	V
		$I_F=100\text{mA}$	—	0.93	1	
		$I_F=200\text{mA}$	—	1.03	1.25	
Total Capacitance	C_T	$V_R=0\text{V}, f=1.0\text{MHz}$	—	1	5	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=30\text{mA}$ $I_{rr}=3.0\text{mA}, R_L=100\Omega$	—	—	50	ns

Notes: 1. Short duration test pulse used to minimize self-heating effect.

2. Part mounted on FR-4 board with recommended pad layout.

High Voltage Surface Mount Switching Diode

